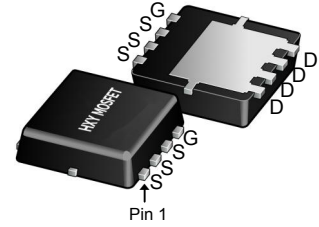




## Description

The AON7264E uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN3X3-8L

## General Features

$V_{DS} = 60V$   $I_D = 40A$

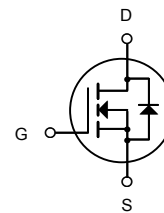
$R_{DS(ON)} < 15m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AON7264E	DFN3X3-8L	40N06 XXYY	5000

## Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	40	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	A
IDM	Pulsed Drain Current <sup>2</sup>	150	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	36	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	30	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	2.5	$^\circ C/W$



**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=20A$	-	12	15	m $\Omega$
		$V_{GS}=4.5V, I_D=10A$	-	15	20	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	930	-	pF
$C_{oss}$	Output Capacitance		-	230	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	8	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=30V, I_D=20A,$ $V_{GS}=10V$	-	22	-	nC
$Q_{gs}$	Gate-Source Charge		-	4.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	3.5	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=20A,$ $R_G=1.6\Omega, V_{GS}=10V$	-	4.5	-	ns
$t_r$	Turn-on Rise Time		-	2.7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	13.8	-	ns
$t_f$	Turn-off Fall Time		-	2.7	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	150	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$T_J=25^\circ\text{C},$ $I_F=20A, di/dt=100A/\mu s$	-	18	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

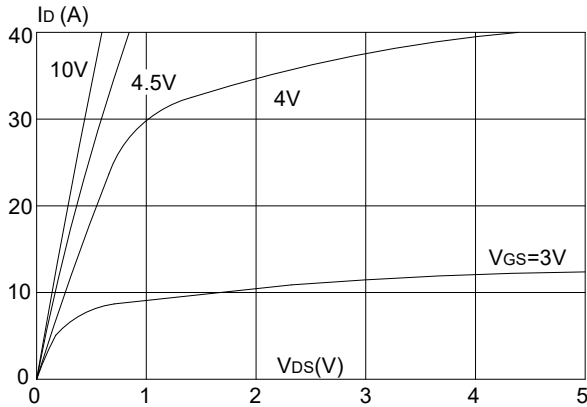
2. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=12A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

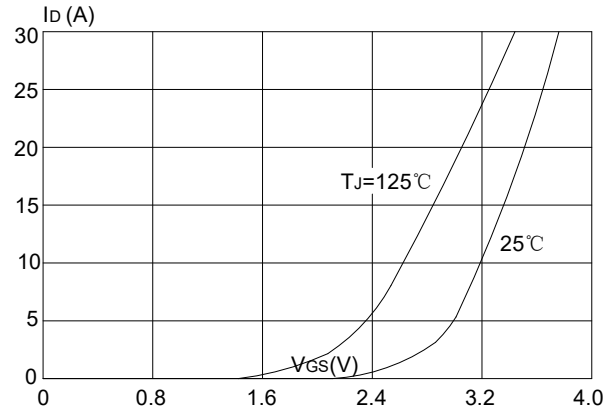


## Typical Performance Characteristics

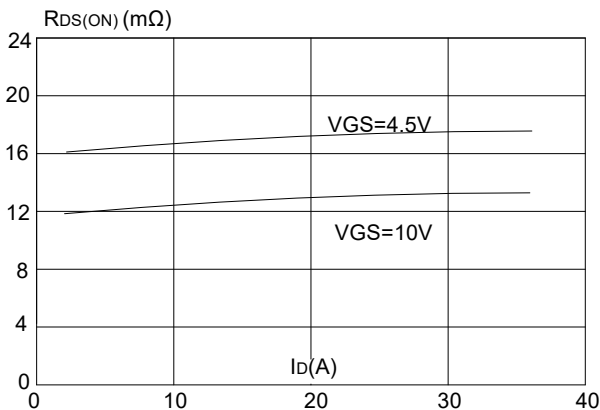
**Figure 1:** Output Characteristics



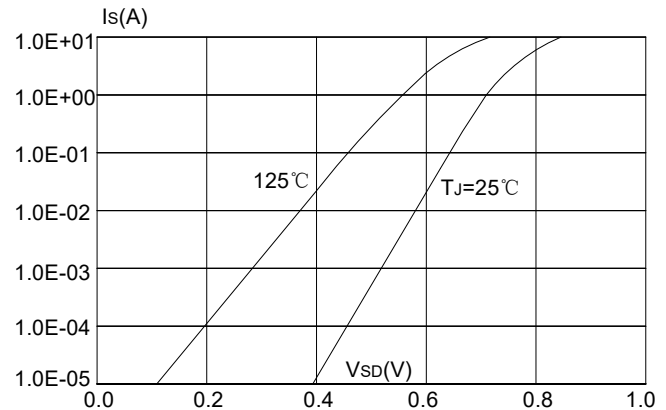
**Figure 2:** Typical Transfer Characteristics



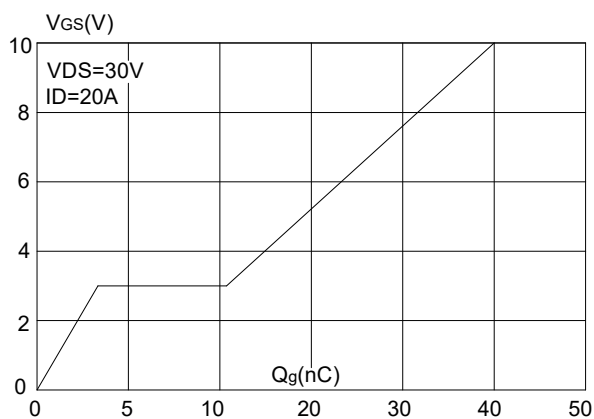
**Figure 3:** On-resistance vs. Drain Current



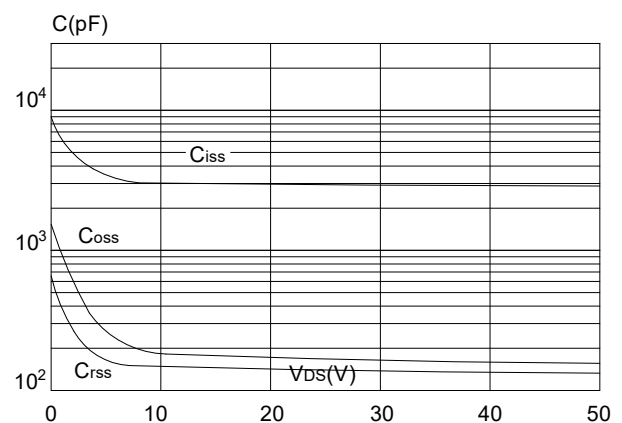
**Figure 4:** Body Diode Characteristics



**Figure 5:** Gate Charge Characteristics

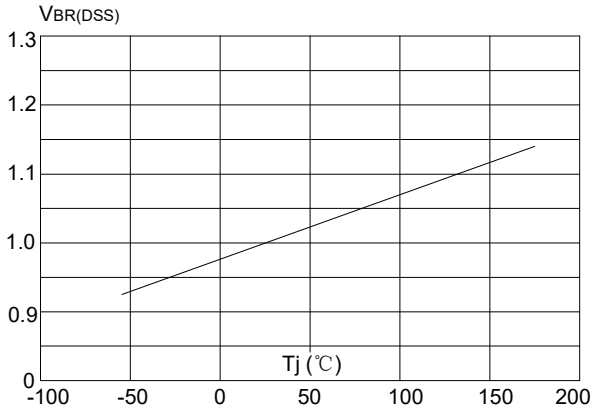


**Figure 6:** Capacitance Characteristics

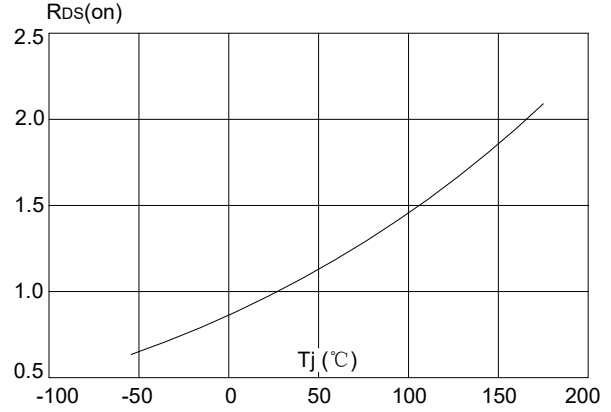




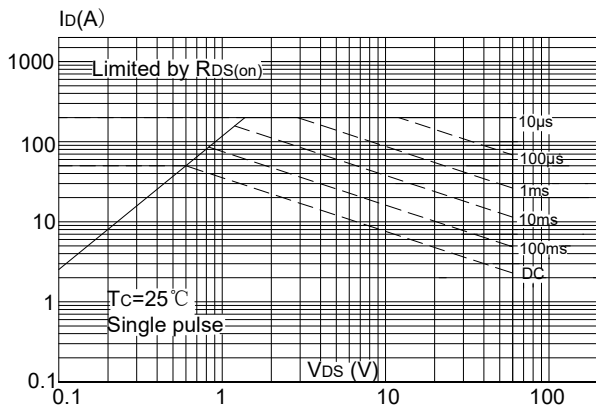
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



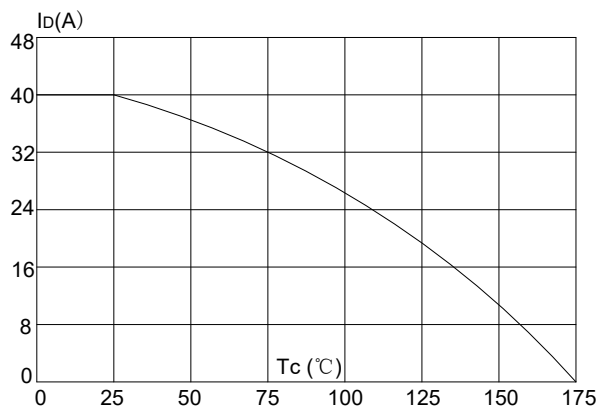
**Figure 8:** Normalized on Resistance vs. Junction Temperature



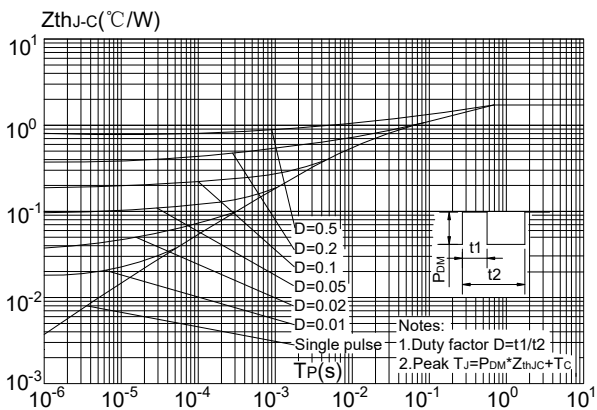
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

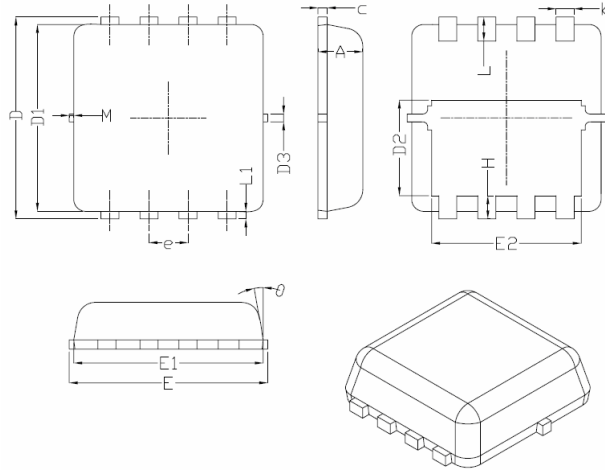


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





### DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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